FORM PTO-1449 (Modified) ATTY. DOCKET NO. SERIAL NO. FIS9-2003-0238US1 10/707,842 LIST OF PATENTS AND PUBLICAT APPLICANT: APPLICANT'S INFORMATION DISCLOSURE Haining S. Yang, et al. STATEMENT GROUP: (Use several sheets if necessary) FILING DATE: 101/16/2004 Unassigned REFERENCE DESIGNATION U.S. PATENT DOCUMENTS FILING DATE **EXAMINER DOCUMENT CLASS** SUBCLASS (IF APPRO.) DATE NAME INITIALS NUMBER 6,228,694 B1 5/8/2001 Doyle et al. 6,406,973 B1 6/18/2002 Lee 8/28/2001 6,281,532 B1 Doyle et al. 5,683,934 11/4/97 Candelaria 4/9/2002 Kuhn, et al. 6,368,931 B1 5,310,446 5/10/94 Konishi et al. 4,853,076 8/1/89 Tsaur et al. US 2002/0090791 A1 7/11/2002 Doyle et al. 6/20/2002 Doyle et al. US 2002/0074598 A1 6,509,618 B2 or/21/2003 Jan et al. 6,476,462 B2 11/5/2002 Shimizu et al. 6,362,082 B1 3/26/2002 Doyle et al. 10/15/96 Asakawa et al. 5,565,697 US 2003/0040158 A1 2/27/2003 Saitoh US 2002/0086472 A1 7/4/2002 Roberds et al. 6,521,964 B1 2/18/2003 Jan et al. 01/14/03 Jan, et al. 6,506,652 FOREIGN PATENT DOCUMENTS **TRANSLATION** DOCUMENT **COUNTRY** CLASS SUBCLASS NUMBER DATE YES NO OTHER ART (Including Author, Title, Date, Pertinent Pages, etc.) EXAMINER DATE CONSIDERED EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if

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	3,602,841	8/31/1971	McGroddy		+ 1		
W	6,531,740	3/11/2003	Bosco, et al.	 			
1/4	6,531,369	3/11/2003	Ozkan, et al.				
WC	6,501,121	12/31/2002	Yu, et al.				
WC	6,498,358	12/24/2002	Lach, et al.				
WL	6,493,497	12/10/2002	Ramdani, et al.	 			-
GU	6,403,975	6/11/2002	Brunner, et al.				
WC	6,361,885	3/26/2002	Chou	-			
WC		7/3/2001	Li, et al.				
W	6,255,169			 			
WL	6,246,095	6/12/2001	Brady, et al.				
WL	6,165,383	12/26/2000	Chou	 			
W_	6,133,071	10/17/2000	Nagai			ļ	+
WC	6,046,464	4/4/2000	Schetzina				_}
W	6,025,280	2/15/2000	Brady, et al.		<u> </u>		<u> </u>
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WL	5,940,736	8/17/1999	Brady, et al.	1	1	. / _		
616	5,880,040	3/9/1999	Sun, et al.					
WL	5,861,651	1/19/1999	Brasen, et al.					
WL	5,679,965	10/21/1997	Schetzina					
TUL	5,670,798	9/23/1997	Schetzina					
WL	5,561,302	10/1/1996	Candelaria					
WL	5,471,948	12/5/1995	Burroughes, et al.					
11/	5,459,346	10/17/1995	Asakawa, et al.					
.WC	5,391,510	2/21/1995	Hsu, et al.					
1.11	5,371,399	12/6/1994	Burroughes, et al.					
1.11	5,108,843	4/28/1992	Ohtaka, et al.		1 1			
1.11	5,060,030	10/22/1991	Hoke			\ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \		
111	4,958,213	9/18/1990	Eklund, et al.	1				
WL	4,665,415	5/12/1987	Esaki, et al.					
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WL	5,989,978	11/23/1999	Peidous		11			
WL	6,284,626	9/4/2001	Kim					
WL	6,274,444	8/14/2001	Wang					
WL	6,261,964	7/17/2001	Wu, et al.					
WL	6,221,735	4/24/2001	Manley, et al.					
WL	6,117,722	9/12/2000	Wuu, et al.					
WL	6,107,143	8/22/2000	Park, et al.					
WL	6,090,684	7/18/2000	Ishitsuka, et al.					
WL	6,066,545	5/23/2000	Doshi, et al.	•				
WL	6,008,126	12/28/1999	Leedy					
WL	5,946,559	8/31/1999	Leedy					
WC	5,840,593	11/24/1998	Leedy					
W	5,592,018	1/7/1997	Leedy					
W	5,592,007	1/7/1997	Leedy					
WC	5,571,741	11/5/1996	Leedy			J		
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WL	Kern Rim, et al., "Characteristics and Device Design of Sub-100 nm Strained Si N- and PMOSFETs", 2002 Symposium On VLSI Technology Digest of Technical Papers, IEEE, pp 98-99.								
WL	Grange Scott et al. "NMOS Drive Current Reduction Caused by Transistor Layout and Transh								
WL	F. Ootsuka, et al., "A Highly Dense, High-Performance 130nm node CMOS Technology for Large Scale System-on-a-Chip Application", International Electron Devices Meeting, 23.5.1, IEEE, April 2000.								
WL	Shinya Ito, et al., "Mechanical Stress Effect of Etch-Stop Nitride and its Impact on Deep Submicron Transistor Design", International Electron Devices Meeting, 10.7.1, IEEE, April 2000.								
CUL	A. Shimizu, et al., "Local Mechanical-Stress Control (LMC): A New Technique for CMOS-Performance Enhancement", International Electron Devices Meeting, IEEE, March 2001.								
WL	K. Ota, et al., "Novel Locally Strained Channel Technique for high Performance 55nm CMOS", International Electron Devices Meeting 2.2.1, IEEE, February 2002.								
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